

Thomas Walther

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

146
papers

2,046
citations

22
h-index

41
g-index

159
ext. papers

2,167
ext. citations

1.8
avg, IF

4.69
L-index

#	Paper	IF	Citations
146	Quantitative microstructural and spectroscopic investigation of inversion domain boundaries in sintered zinc oxide ceramics doped with iron oxide. <i>International Journal of Materials Research</i> , 2022 , 97, 934-942	0.5	
145	Failure Analysis of Some Commercial Spotlights Based on Light Emitting Diodes. <i>Electronics (Switzerland)</i> , 2022 , 11, 48	2.6	1
144	X-ray mapping in a scanning transmission electron microscope of InGaAs quantum dots with embedded fractional monolayers of aluminium. <i>Semiconductor Science and Technology</i> , 2020 , 35, 084001	1.8	1
143	Preface for the special issue on Microscopy of Semiconducting Materials 2019. <i>Semiconductor Science and Technology</i> , 2020 , 35, 120201	1.8	
142	Measuring grain boundary segregation: tomographic atom probe field ion microscopy (APFIM) vs. analytical scanning transmission electron microscopy (STEM). <i>Journal of Physics: Conference Series</i> , 2019 , 1190, 012002	0.3	
141	Measurement of Diffusion and Segregation in Semiconductor Quantum Dots and Quantum Wells by Transmission Electron Microscopy: A Guide. <i>Nanomaterials</i> , 2019 , 9,	5.4	3
140	Comment on Nanoscale mapping of optical band gaps using monochromated electron energy loss spectroscopy. <i>Nanotechnology</i> , 2018 , 29, 318001	3.4	1
139	Stranski-Krastanov growth of (Si)Ge/Si(001): transmission electron microscopy compared with segregation theory. <i>Materials Science and Technology</i> , 2018 , 34, 1539-1548	1.5	3
138	Self-consistent absorption correction for quantifying very noisy X-ray maps: group III nitride nanowires as an example. <i>Journal of Microscopy</i> , 2018 , 272, 111-122	1.9	3
137	Correlating compositional, structural and optical properties of InGaN quantum wells by transmission electron microscopy 2018 , 267-272		
136	Electron energy loss spectroscopic profiling of semiconductor hetero- and nano-structures: theory, implementation, applications 2018 , 27-32		
135	How InGaAs islands form on GaAs substrates: the missing link in the explanation of the Stranski-Krastanow transition 2018 , 85-88		
134	Study of phase separation in an InGaN alloy by electron energy loss spectroscopy in an aberration corrected monochromated scanning transmission electron microscope. <i>Journal of Materials Research</i> , 2017 , 32, 983-995	2.5	10
133	Transmission electron microscopy of AlGaAs/GaAs quantum cascade laser structures. <i>Journal of Microscopy</i> , 2017 , 268, 298-304	1.9	6
132	Effective absorption correction for energy dispersive X-ray mapping in a scanning transmission electron microscope: analysing the local indium distribution in rough samples of InGaN alloy layers. <i>Journal of Microscopy</i> , 2017 , 268, 248-253	1.9	3
131	Comparison of cross-sectional transmission electron microscope studies of thin germanium epilayers grown on differently oriented silicon wafers. <i>Journal of Microscopy</i> , 2017 , 268, 288-297	1.9	4
130	Transmission Electron Microscopy of Nanostructures 2017 , 105-134		4

129	Preface to special issue on Microscopy of Semiconducting Materials 2017 (MSM-XX). <i>Journal of Microscopy</i> , 2017 , 268, 221-224	1.9	1
128	Evidence of terbium and oxygen co-segregation in annealed AlN:Tb. <i>Applied Physics Letters</i> , 2017 , 110, 222102	3.4	4
127	Preface of 19(th) Microscopy of Semiconducting Materials conference. <i>Journal of Microscopy</i> , 2016 , 262, 131-3	1.9	1
126	Joint plasmon and core-loss fitting for electron energy loss spectroscopy of InGaN 2016 , 893-894		
125	Influence of background subtraction and deconvolution on calculation of EELS core-loss intensities 2016 , 891-892		
124	Investigation of phase separation in InGaN alloys by plasmon loss spectroscopy in a TEM. <i>MRS Advances</i> , 2016 , 1, 2749-2756	0.7	3
123	Automated background subtraction technique for electron energy-loss spectroscopy and application to semiconductor heterostructures. <i>Journal of Microscopy</i> , 2016 , 262, 157-66	1.9	5
122	Self-consistent method for quantifying indium content from X-ray spectra of thick compound semiconductor specimens in a transmission electron microscope. <i>Journal of Microscopy</i> , 2016 , 262, 151-6 ^{1.9}		13
121	What environmental transmission electron microscopy measures and how this links to diffusivity: thermodynamics versus kinetics. <i>Journal of Microscopy</i> , 2015 , 257, 87-91	1.9	3
120	Twinning in GaAs nanowires on patterned GaAs(111)B. <i>Crystal Research and Technology</i> , 2015 , 50, 62-68	1.3	3
119	Microscopy of Semiconducting Materials 2015. <i>Semiconductor Science and Technology</i> , 2015 , 30, 110301	1.8	2
118	Scanning transmission electron microscopy measurement of bismuth segregation in thin Ga(As,Bi) layers grown by molecular beam epitaxy. <i>Crystal Research and Technology</i> , 2015 , 50, 38-42	1.3	6
117	Electron microscopy of quantum dots. <i>Journal of Microscopy</i> , 2015 , 257, 171-8	1.9	6
116	Defects, strain relaxation, and compositional grading in high indium content InGaN epilayers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 118, 155301	2.5	34
115	New pathways for improved quantification of energy-dispersive X-ray spectra of semiconductors with multiple X-ray lines from thin foils investigated in transmission electron microscopy. <i>Journal of Microscopy</i> , 2015 , 260, 427-41	1.9	5
114	Combination of electron energy-loss spectroscopy and energy dispersive x-ray spectroscopy to determine indium concentration in InGaN thin film structures. <i>Semiconductor Science and Technology</i> , 2015 , 30, 114011	1.8	5
113	Nanostructure and strain properties of core-shell GaAs/AlGaAs nanowires. <i>Semiconductor Science and Technology</i> , 2015 , 30, 114012	1.8	5
112	Self-consistent absorption correction for quantitative energy- dispersive X-ray spectroscopy of InGaN layers in analytical transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , 2015 , 644, 012006	0.3	3

111	Accurate measurement of atomic segregation to grain boundaries or to planar faults by analytical transmission electron microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 310-313		3
110	Concentration quenching of the luminescence from trivalent thulium, terbium, and erbium ions embedded in an AlN matrix. <i>Journal of Luminescence</i> , 2014 , 145, 855-858	3.8	9
109	Similarity of Stranski-Krastanow growth of Ge/Si and SiGe/Si (001). <i>Journal of Applied Physics</i> , 2014 , 115, 012003	2.5	9
108	The influence of emitter conditioning on the performance of a tungsten cold field emission gun operating at 300 kV. <i>Journal of Physics: Conference Series</i> , 2014 , 522, 012053	0.3	
107	How to best measure atomic segregation to grain boundaries by analytical transmission electron microscopy. <i>Journal of Materials Science</i> , 2014 , 49, 3898-3908	4.3	7
106	Lattice resolved annular dark-field scanning transmission electron microscopy of (Al, In)GaN/GaN layers for measuring segregation with sub-monolayer precision. <i>Journal of Materials Science</i> , 2013 , 48, 2883-2892	4.3	14
105	The Stranski-Krastanow transition in SiGe epitaxy investigated by scanning transmission electron microscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 187-190	1.6	5
104	Aberration Corrected High-Resolution Transmission and Scanning Transmission Electron Microscopy of Thin Perovskite Layers. <i>Physics Procedia</i> , 2013 , 40, 49-55		4
103	Homogeneous array of nanowire-embedded quantum light emitters. <i>Nano Letters</i> , 2013 , 13, 861-5	11.5	33
102	Controlled Quantum Dot Formation on Focused Ion Beam-Patterned GaAs Substrates. <i>Lecture Notes in Nanoscale Science and Technology</i> , 2013 , 299-314	0.3	
101	GaN-based radial heterostructure nanowires grown by MBE and ALD. <i>Journal of Physics: Conference Series</i> , 2013 , 471, 012039	0.3	1
100	Study of site controlled quantum dot formation on focused ion beam patterned GaAs substrate. <i>Journal of Physics: Conference Series</i> , 2013 , 471, 012047	0.3	3
99	Towards the structure of rare earth luminescence centres in terbium doped aluminium nitride as an example system. <i>Journal of Physics: Conference Series</i> , 2013 , 471, 012032	0.3	4
98	Investigation of growth of thin layers of perovskite on native silicon dioxide by a combination of atomic force microscopy and transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , 2013 , 471, 012037	0.3	
97	Calibration of thickness-dependent k-factors for germanium X-ray lines to improve energy-dispersive X-ray spectroscopy of SiGe layers in analytical transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , 2013 , 471, 012031	0.3	5
96	Epitaxial growth of relaxed germanium layers by reduced pressure chemical vapour deposition on (110) and (111) silicon substrates. <i>Thin Solid Films</i> , 2012 , 520, 3222-3226	2.2	18
95	Measurement of the Al content in AlGaIn epitaxial layers by combined energy-dispersive X-ray and electron energy-loss spectroscopy in a transmission electron microscope. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1079-1082		6
94	Characterization of InGaIn/GaN epitaxial layers by aberration corrected TEM/STEM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 546-549		10

93	Characterization of thickness, elemental distribution and band-gap properties in AlGa _N /Ga _N quantum wells by aberration-corrected TEM/STEM. <i>Journal of Physics: Conference Series</i> , 2012 , 371, 012014	0.3	1
92	Self-consistent absorption corrections for low-energy X-ray lines in energy-dispersive X-ray spectroscopy. <i>Journal of Physics: Conference Series</i> , 2012 , 371, 012063	0.3	1
91	Configuring a 300kV cold field-emission gun for optimum analytical performance. <i>Journal of Physics: Conference Series</i> , 2012 , 371, 012012	0.3	4
90	Performance of a cold-field emission gun double aberration corrected TEM/STEM at 80kV. <i>Journal of Physics: Conference Series</i> , 2012 , 371, 012013	0.3	1
89	Analysis of partially oxidised epitaxial silicon mono-layers on germanium virtual substrates using aberration corrected scanning transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012050	0.3	
88	GaAsBi atomic surface order and interfacial roughness observed by STM and TEM. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012060	0.3	3
87	Quantification of series of X-ray spectra taken at different tilts in analytical transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012037	0.3	
86	Nanoscale EELS analysis of elemental distribution and band-gap properties in AlGa _N epitaxial layers. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012039	0.3	6
85	Investigation of boron implantation into silicon by quantitative energy-filtered transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012053	0.3	1
84	A TEM study of Ge-on-(111)Si structures for potential use in high performance PMOS device technology. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012023	0.3	1
83	Comparison of the contrast in conventional and lattice resolved ADF STEM images of InGaAs/GaAs structures using different camera lengths. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012041	0.3	4
82	Room-Temperature GaAs/AlGaAs Quantum Cascade Lasers Grown by MetalOrganic Vapor Phase Epitaxy. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 774-776	2.2	9
81	Accurate calibration for the quantification of the Al content in AlGa _N epitaxial layers by energy-dispersive X-ray spectroscopy in a Transmission Electron Microscope. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012028	0.3	2
80	High Repetition Rate Ti:Sapphire Laser Mode-Locked by InP Quantum-Dot Saturable Absorber. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 1603-1605	2.2	8
79	Direct observation by transmission electron microscopy of the influence of Ni catalyst-seeds on the growth of Ga _N /AlGa _N axial heterostructure nanowires. <i>Journal of Crystal Growth</i> , 2011 , 327, 27-34	1.6	4
78	High temperature ~4 [micro sign]m In _{0.7} Ga _{0.3} As/In _{0.34} Al _{0.66} As quantum cascade lasers grown by MOVPE. <i>Electronics Letters</i> , 2011 , 47, 559	1.1	2
77	17th International Conference on Microscopy of Semiconducting Materials 2011. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 011001	0.3	2
76	Study of annealed InAs/GaAs quantum dot structures. <i>Journal of Physics: Conference Series</i> , 2010 , 209, 012036	0.3	6

75	An improved approach to quantitative X-ray microanalysis in (S)TEM: Thickness dependent k-factors. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012016	0.3	6
74	GaN, AlGaN, HfO ₂ based radial heterostructure nanowires. <i>Journal of Physics: Conference Series</i> , 2010 , 209, 012011	0.3	6
73	TEM analysis of Ge-on-Si MOSFET structures with HfO ₂ dielectric for high performance PMOS device technology. <i>Journal of Physics: Conference Series</i> , 2010 , 209, 012061	0.3	1
72	Quantitative investigation of the onset of islanding in strained layer epitaxy of InAs/GaAs by X-ray mapping in STEM. <i>Journal of Physics: Conference Series</i> , 2010 , 209, 012035	0.3	4
71	Probe position recovery for ptychographical imaging. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012004	0.3	10
70	Study of the effect of annealing of In(Ga)As quantum dots. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012054	0.3	2
69	Measuring the contrast in annular dark field STEM images as a function of camera length. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012068	0.3	3
68	STEM imaging of InP/AlGaInP quantum dots. <i>Journal of Physics: Conference Series</i> , 2010 , 245, 012087	0.3	2
67	TEM analysis of Si-passivated Ge-on-Si MOSFET structures for high performance PMOS device technology. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012044	0.3	
66	Electron microscopy of AlGaN-based multilayers for UV laser devices. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012048	0.3	
65	Comparison of experimental and theoretical X-ray intensities from (In)GaAs specimens investigated by energy-dispersive X-ray spectroscopy in a transmission electron microscope. <i>Journal of Physics: Conference Series</i> , 2010 , 209, 012029	0.3	6
64	Quantification of carbon contamination under electron beam irradiation in a scanning transmission electron microscope and its suppression by plasma cleaning. <i>Journal of Physics: Conference Series</i> , 2010 , 241, 012017	0.3	23
63	Influence of thick crystal effects on ptychographic image reconstruction with moveable illumination. <i>Ultramicroscopy</i> , 2009 , 109, 1263-75	3.1	19
62	A simple method to improve the quantification accuracy of energy-dispersive X-ray microanalysis. <i>Journal of Physics: Conference Series</i> , 2008 , 126, 012090	0.3	5
61	1.55 μ m InAs quantum dots grown on a GaAs substrate using a GaAsSb metamorphic buffer layer. <i>Applied Physics Letters</i> , 2008 , 92, 111906	3.4	35
60	A comparison of transmission electron microscopy methods to measure wetting layer thicknesses to sub-monolayer precision. <i>Journal of Physics: Conference Series</i> , 2008 , 126, 012091	0.3	3
59	Quantifying the Top-Bottom Effect in Energy-Dispersive X-Ray Spectroscopy of Nanostructures Embedded in Thin Films. <i>Springer Proceedings in Physics</i> , 2008 , 185-188	0.2	
58	Comparison of monochromated electron energy-loss with X-ray absorption near-edge spectra: ELNES vs. XANES 2008 , 65-66		

57	Comparison of transmission electron microscopy methods to measure layer thicknesses to sub-monolayer precision 2008 , 377-378		
56	TEM Characterization of ZnO Nanorods. <i>Springer Proceedings in Physics</i> , 2008 , 247-250	0.2	2
55	Investigating the Capping of InAs Quantum Dots by InGaAs. <i>Springer Proceedings in Physics</i> , 2008 , 259-262	2.2	3
54	Structural and Compositional Properties of Strain-Symmetrized SiGe/Si Heterostructures. <i>Springer Proceedings in Physics</i> , 2008 , 269-272	0.2	1
53	Electro-Assisted Photo-Luminescence of Colloidal Germanium Nanoparticles. <i>Zeitschrift Fur Physikalische Chemie</i> , 2007 , 221, 377-386	3.1	0
52	Combinatorial investigation of the isolated nanoparticle to coalescent layer transition in a gradient sputtered gold nanoparticle layer on top of polystyrene. <i>Applied Physics Letters</i> , 2006 , 88, 021910	3.4	40
51	Laser-assisted synthesis of Au-Ag alloy nanoparticles in solution. <i>Journal of Physical Chemistry B</i> , 2006 , 110, 2549-54	3.4	92
50	Preliminary results from the first monochromated and aberration corrected 200-kV field-emission scanning transmission electron microscope. <i>Microscopy and Microanalysis</i> , 2006 , 12, 498-505	0.5	19
49	A new experimental procedure to quantify annular dark field images in scanning transmission electron microscopy. <i>Journal of Microscopy</i> , 2006 , 221, 137-44	1.9	43
48	Linear least-squares fit evaluation of series of analytical spectra from planar defects: extension and possible implementations in scanning transmission electron microscopy. <i>Journal of Microscopy</i> , 2006 , 223, 165-70	1.9	10
47	High ultimate tensile stress in nano-grained superelastic NiTi thin films. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2006 , 415, 304-308	5.3	17
46	Structure of PtFe/Fe double-period multilayers investigated by X-ray diffraction, reflectivity, diffuse scattering and TEM. <i>Applied Surface Science</i> , 2006 , 253, 128-132	6.7	7
45	First experimental test of a new monochromated and aberration-corrected 200 kV field-emission scanning transmission electron microscope. <i>Ultramicroscopy</i> , 2006 , 106, 963-9	3.1	27
44	Structural and magnetic characteristics of FeCo thin films modified by combinatorial ion implantation. <i>Thin Solid Films</i> , 2006 , 495, 169-174	2.2	8
43	A Novel Method of Analytical Transmission Electron Microscopy for Measuring Highly Accurately Segregation to Special Grain Boundaries or Planar Interfaces. <i>Mikrochimica Acta</i> , 2006 , 155, 313-318	5.8	9
42	Quantitative microstructural and spectroscopic investigation of inversion domain boundaries in sintered zinc oxide ceramics doped with iron oxide. <i>International Journal of Materials Research</i> , 2006 , 97, 934-942	0.5	16
41	The Mechanism of the Stranski-Krastanov Transition 2005 , 71-88		
40	Photofragmentation of phase-transferred gold nanoparticles by intense pulsed laser light. <i>Journal of Physical Chemistry B</i> , 2005 , 109, 15735-40	3.4	35

39	Critical assessment of the speckle statistics in fluctuation electron microscopy and comparison to electron diffraction. <i>Ultramicroscopy</i> , 2005 , 104, 206-19	3.1	9
38	Influence of intense pulsed laser irradiation on optical and morphological properties of gold nanoparticle aggregates produced by surface acid-base reactions. <i>Langmuir</i> , 2005 , 21, 4249-53	4	35
37	Stripe TEM as a method of calculating chemical profiles across interfaces between solids or core-shell structures using electron energy-loss spectroscopic profiling. <i>International Journal of Materials Research</i> , 2005 , 96, 429-437		3
36	ConceptEM: a new method to quantify solute segregation to interfaces or planar defect structures by analytical TEM and applications to inversion domain boundaries in doped zinc oxide 2005 , 199-202		3
35	Diffusion and segregation effects in doped manganite/titanate heterostructures. <i>Applied Physics Letters</i> , 2004 , 84, 3882-3884	3.4	25
34	Development of a new analytical electron microscopy technique to quantify the chemistry of planar defects and to measure accurately solute segregation to grain boundaries. <i>Journal of Microscopy</i> , 2004 , 215, 191-202	1.9	22
33	Twin Boundaries in Zinc Oxide with Additions of Gallium Oxide. <i>Journal of Materials Science</i> , 2004 , 12, 213-226		14
32	A New Method to Measure Small Amounts of Solute Atoms on Planar Defects and Application to Inversion Domain Boundaries in Doped Zinc Oxide. <i>Journal of Materials Science</i> , 2004 , 12, 267-275		24
31	Application of quantitative analytical electron microscopy to the mineral content of insect cuticle. <i>Microscopy and Microanalysis</i> , 2003 , 9, 152-4	0.5	5
30	Strategies for investigating core-shell particles by energy-filtered transmission electron microscopy. <i>Microscopy and Microanalysis</i> , 2003 , 9, 98-99	0.5	
29	Atomic structure of basal-plane inversion boundaries in SnO ₂ -doped ZnO. <i>Microscopy and Microanalysis</i> , 2003 , 9, 286-287	0.5	4
28	Behavior of basic refractories at high temperatures in steelmaking processes thermodynamics and implications for the usability of olivine as refractory material. <i>European Journal of Mineralogy</i> , 2003 , 15, 193-205	2.2	5
27	Fluctuation Electron Microscopy on a-Ge and Polycrystalline Gold. <i>Microscopy and Microanalysis</i> , 2003 , 9, 152-153	0.5	7
26	Electron energy-loss spectroscopic profiling of thin film structures: 0.39 nm line resolution and 0.04 eV precision measurement of near-edge structure shifts at interfaces. <i>Ultramicroscopy</i> , 2003 , 96, 401-11 ^{3.1}		35
25	Influence of pumping and inherent laser light on properties and degradation of ZnMgSSe/ZnSe quantum well heterostructures. <i>Physica Status Solidi A</i> , 2003 , 195, 188-193		1
24	Structural and doping effects in the half-metallic double perovskite A ₂ CrWO ₆ (A=Sr, Ba, and Ca). <i>Physical Review B</i> , 2003 , 68,	3.3	290
23	Combinatorial Thin Film Synthesis of NiMnAl Magnetic Shape Memory Alloys Using MBE Technique. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 785, 231		
22	Stranski-Krastanow transition and epitaxial island growth. <i>Physical Review B</i> , 2002 , 66,	3.3	109

21	Microstructure and magnetoresistance of epitaxial films of the layered perovskite $\text{La}_{2-x}\text{Sr}_{1+2x}\text{Mn}_2\text{O}_7$ ($x=0.3$ and 0.4). <i>Physical Review B</i> , 2002 , 65,	3.3	20
20	Measurement of diffusion lengths in quaternary semiconducting thin layers by spectrum imaging. <i>Physica B: Condensed Matter</i> , 2001 , 308-310, 1161-1164	2.8	2
19	Thermal Stability of ZnMgSSe/ZnSe Laser Heterostructures. <i>Physica Status Solidi A</i> , 2001 , 185, 301-308		3
18	Auger depth profile analysis and EFTEM analysis of annealed Ti/Al-contacts on Si-doped GaN. <i>Applied Surface Science</i> , 2001 , 179, 213-221	6.7	7
17	Structure and Chemistry of Basal-Plane Inversion Boundaries in Antimony Oxide-Doped Zinc Oxide. <i>Journal of the American Ceramic Society</i> , 2001 , 84, 2657-2668	3.8	68
16	Nature of the Stranski-Krastanow transition during epitaxy of InGaAs on GaAs. <i>Physical Review Letters</i> , 2001 , 86, 2381-4	7.4	220
15	Epitaxial Island Growth and the Stranski-Krastanow Transition. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 696, 1		
14	The nature of islanding in the InGaAs / GaAs epitaxial system. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 648, 1		0
13	A Study of Sulphur Diffusion in ZnMgSSe/ZnSe Quantum Wells by Energy-Loss Imaging in a Transmission Electron Microscope. <i>Physica Status Solidi A</i> , 2000 , 180, 351-356		8
12	Coexistence of clusters, GPB zones, S_2^- , S_1^- and S-phases in an Al _{0.9%} Cu _{1.4%} Mg alloy. <i>Acta Materialia</i> , 2000 , 48, 2751-2764	8.4	134
11	Diffusion Processes in Strained Silicon Germanium Island Structures. <i>Defect and Diffusion Forum</i> , 2000 , 183-185, 53-60	0.7	2
10	A quantitative study of compositional profiles of chemical vapour-deposited strained silicon/germanium/silicon layers by transmission electron microscopy. <i>Journal of Crystal Growth</i> , 1999 , 197, 113-128	1.6	41
9	Measurement of Oxygen Disorder and Nano-Twin Microstructure Associated with Columnar Defects in YBCO. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 540, 267		1
8	Observation of vertical and lateral Ge segregation in thin undulating SiGe layers on Si by electron energy-loss spectroscopy. <i>Applied Physics Letters</i> , 1997 , 71, 809-811	3.4	82
7	Diffusion and Surface Segregation in Thin SiGe/Si Layers Studied by Scanning Transmission Electron Microscopy. <i>Defect and Diffusion Forum</i> , 1997 , 143-147, 1135-1140	0.7	19
6	Transmission electron microscopy study of Si Doped GaAs/AlGaAs/InGaAs/GaAs pseudomorphic high electron mobility transistor structures. <i>Thin Solid Films</i> , 1997 , 307, 6-9	2.2	2
5	The Scattering Distribution from Semiconductors as a Function of Angle and Energy Loss in the Electron Microscope. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 466, 113		2
4	Changes of the local oxygen content and ordering at twin boundaries of high-Tc YBa ₂ Cu ₃ O _{7-x} superconductors. <i>Physical Review B</i> , 1996 , 54, 16234-16237	3.3	7

3	A Correlation between Compositional Fluctuations and Surface Undulations in Strained Layer Epitaxy. <i>Materials Science Forum</i> , 1995 , 196-201, 505-510	0.4	30
2	Detection of random alloy fluctuations in high-resolution transmission electron micrographs of AlGaAs. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1995 , 72, 1015-1030		9
1	Quantitative characterization of AlAs/GaAs interfaces by high-resolution transmission electron microscopy along the <100> and the <110> projection. <i>Applied Physics A: Solids and Surfaces</i> , 1993 , 57, 393-400		15